



SEMITOP[®] 3

IGBT Module

SK30GD128

Preliminary Data

Features

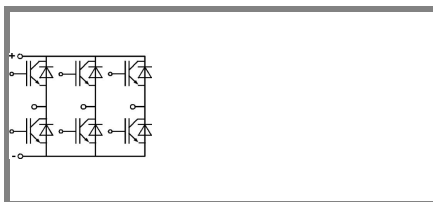
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- High short circuit capability
- SPT = Soft-Punch-Through technology
- $V_{CE,sat}$ with positive coefficient

Typical Applications*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS

Remarks

- V_F = chip level value



GD

Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}	$T_j = 25\text{ °C}$	1200		V
I_C	$T_j = 125\text{ °C}$	$T_s = 25\text{ °C}$	35	A
		$T_s = 80\text{ °C}$	25	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	50		A
V_{GES}		± 20		V
t_{psc}	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125\text{ °C}$ $V_{CES} < 1200\text{ V}$	10		µs
Inverse Diode				
I_F	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$	37	A
		$T_s = 80\text{ °C}$	25	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$			A
I_{FSM}	$t_p = 10\text{ ms}; \text{half sine wave } T_j = 150\text{ °C}$	180		A
Module				
$I_{t(RMS)}$				A
T_{vj}		-40 ... +150		°C
T_{stg}		-40 ... +125		°C
V_{isol}	AC, 1 min.	2500		V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units	
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1\text{ mA}$	4,5	5,5	6,5	V	
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	$T_j = 25\text{ °C}$	0,1		mA	
		$T_j = 125\text{ °C}$	0,1		mA	
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$			200	nA	
V_{CE0}		$T_j = 25\text{ °C}$	1,15		V	
		$T_j = 125\text{ °C}$	1		V	
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	24		mΩ	
		$T_j = 125\text{ °C}$	44		mΩ	
$V_{CE(sat)}$	$I_{Cnom} = 25\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$	1,9		V	
		$T_j = 125\text{ °C}_{chiplev.}$	2,1		V	
C_{ies}	$V_{CE} = 25, V_{GE} = 0\text{ V}$			1,9	nF	
C_{oes}				0,16	nF	
C_{res}				0,09	nF	
Q_G	$V_{GE} = 0...20\text{ V}$			296	nC	
$t_{d(on)}$	$R_{Gon} = 15\text{ } \Omega$	$V_{CC} = 600\text{ V}$ $I_C = 30\text{ A}$			55	ns
t_r					26	ns
E_{on}	$R_{Goff} = 15\text{ } \Omega$	$T_j = 125\text{ °C}$ $V_{GE} = \pm 15\text{ V}$			2,8	mJ
$t_{d(off)}$					284	ns
t_f					40	ns
E_{off}					2,19	mJ
$R_{th(j-s)}$	per IGBT			1	K/W	



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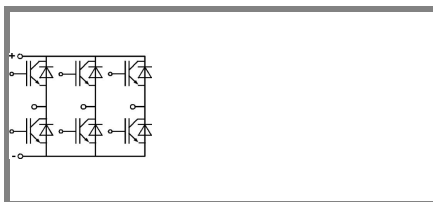
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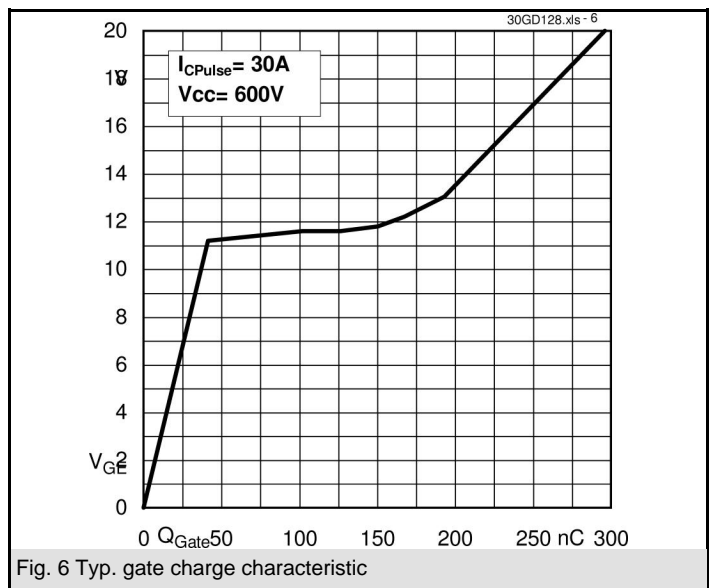
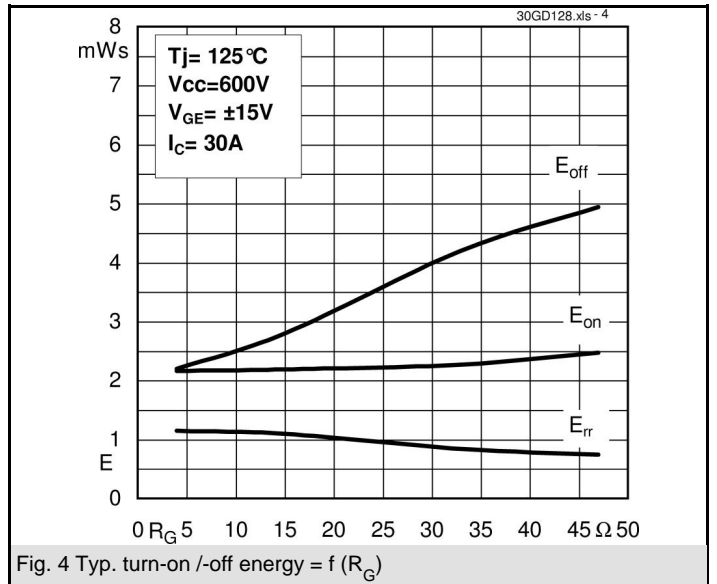
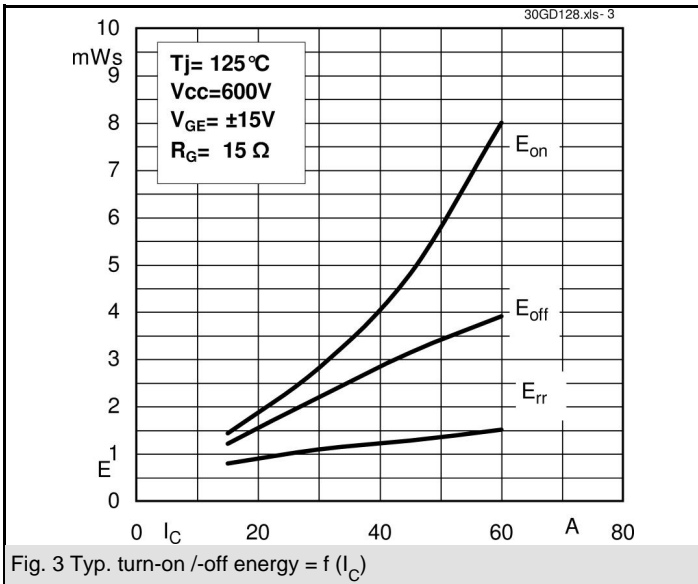
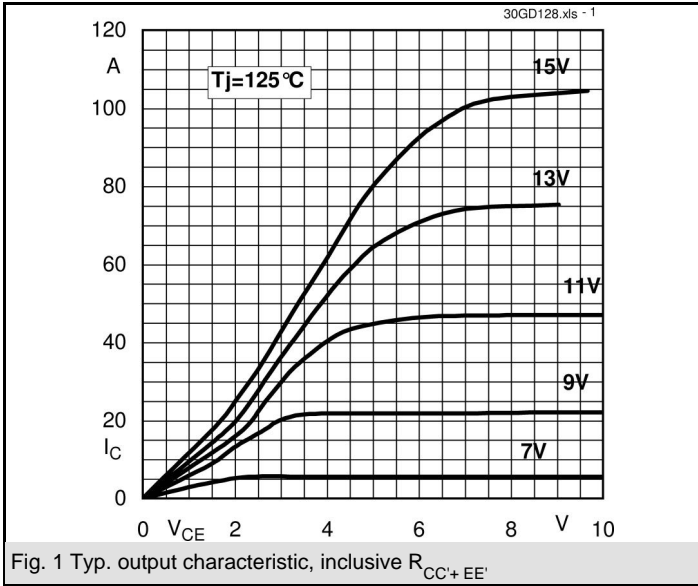
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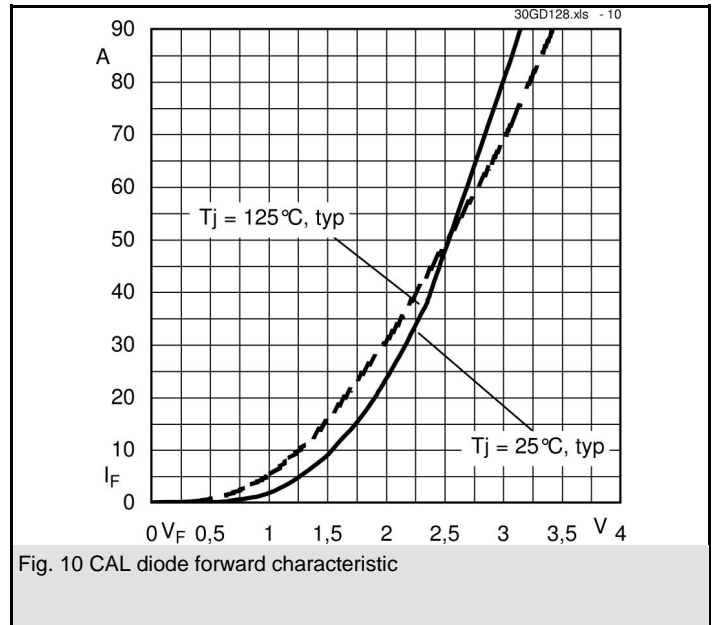
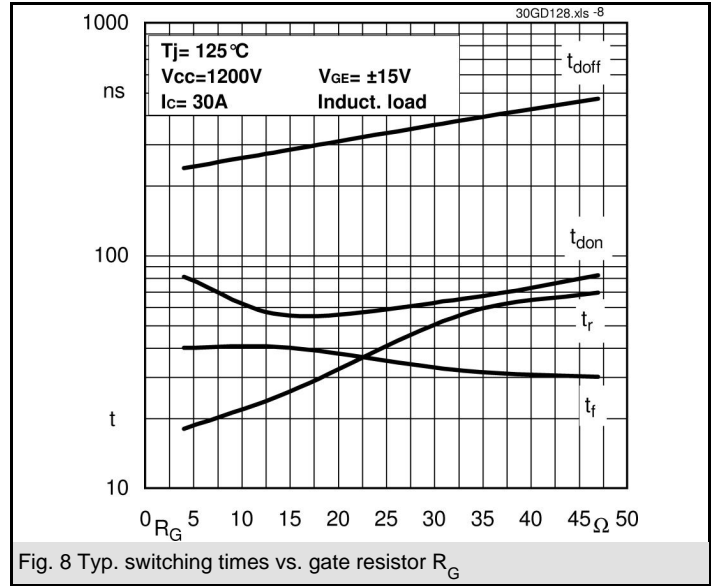
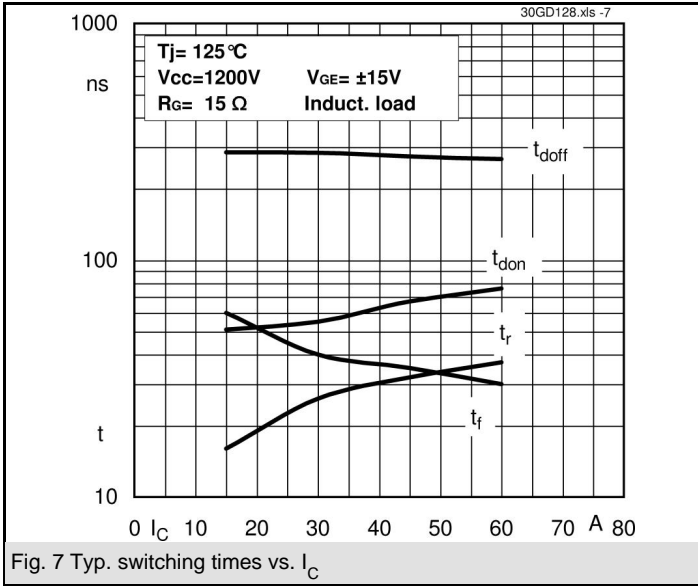
Characteristics

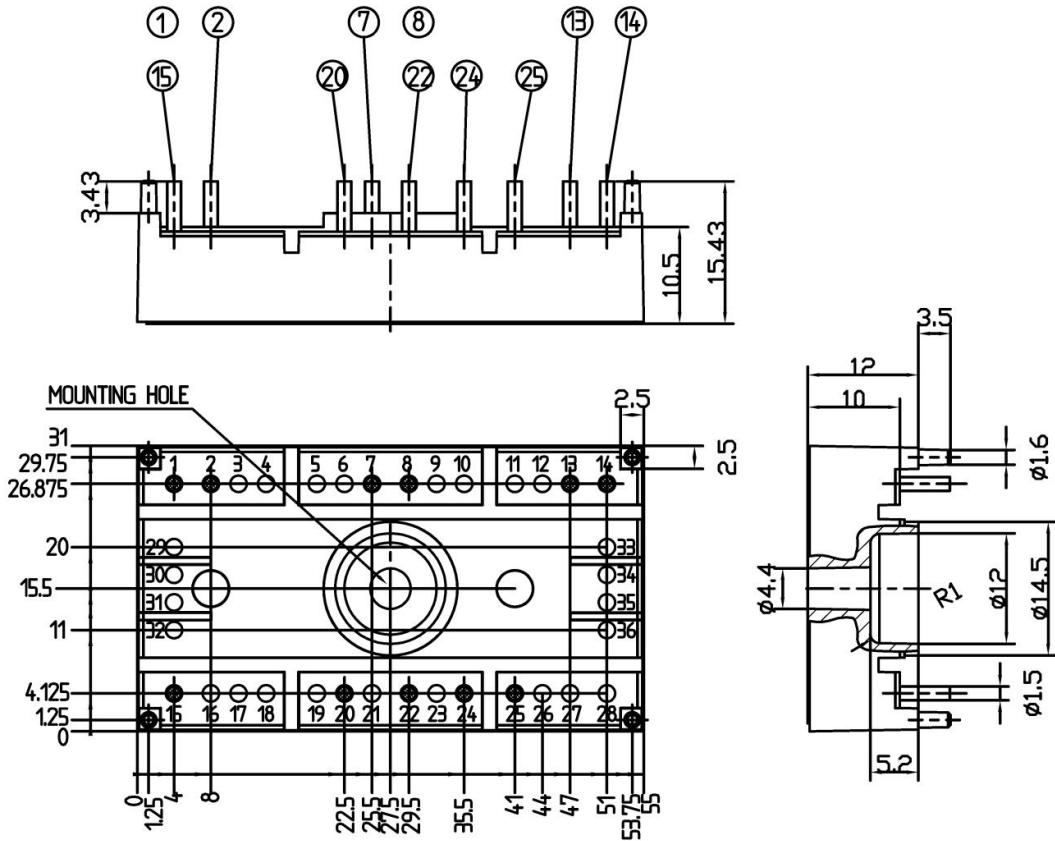
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 25 \text{ A}; V_{GE} = 0 \text{ V}$		2		V
			1,8		V
					$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$
					$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$
V_{F0}			1	1,2	V
r_F			32	44	m Ω
					$T_j = 125 \text{ }^\circ\text{C}$
I_{RRM}	$I_F = 22 \text{ A}$		25		A
Q_{rr}	$di/dt = -500 \text{ A}/\mu\text{s}$		4,5		μC
E_{rr}	$V_{CC} = 600\text{V}$		1		mJ
$R_{th(j-s)D}$	per diode			1,2	K/W
M_s	to heat sink M1			2	Nm
w			19		g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

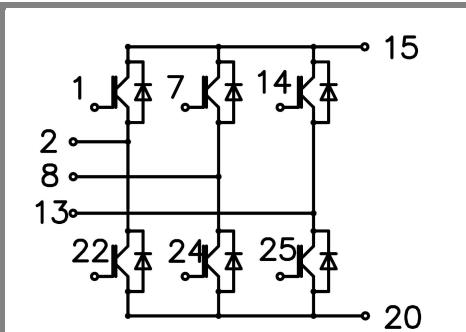
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.







Case T12 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T12

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